

LMV651/LMV652/LMV654 12 MHz, Low Voltage, Low Power Amplifier

General Description

National's LMV651/LMV652/LMV654 are high performance, low power operational amplifier ICs implemented with National's advanced VIP50 process. This family of parts features 12 MHz of bandwidth while consuming only 116 μA of current, which is an exceptional bandwidth to power ratio in this op amp class. The LMV651/LMV652/LMV654 are unity gain stable and provide an excellent solution for general purpose amplification in low voltage, low power applications.

This family of low voltage, low power amplifiers provides superior performance and economy in terms of power and space usage. These op amps have a maximum input offset voltage of 1.5 mV, a rail-to-rail output stage and an input common-mode voltage range that includes ground. The LMV651/LMV652/LMV654 provide a PSRR of 95 dB, a CMRR of 100 dB and a total harmonic distortion (THD) of 0.003% at 1 kHz frequency and 2 $k\Omega$ load.

The operating supply voltage range for this family of parts is from 2.7V and 5.5V. These op amps can operate over a wide temperature range (-40°C to +125°C) making these op amps ideal for automotive applications, sensor applications and portable equipment applications. The LMV651 is offered in the ultra tiny 5-Pin SC70 package, which is about half the size of the 5-Pin SOT23. The LMV652 is offered in an 8-Pin MSOP package. The LMV654 is offered in a 14-Pin TSSOP package.

Features

(Typical 5V supply, unless otherwise noted)

- Guaranteed 3.0V and 5.0V performance
- Low power supply current

— LMV651
 — LMV652
 — LMV654
 118 μA per amplifier
 123 μA per amplifier

— LMV654 122 μA per amplifier High unity gain bandwidth 12 MHz

Max input offset voltageCMRR1.5 mV100 dB

■ PSRR 95 dB
■ Input referred voltage noise 17 nV/√Hz

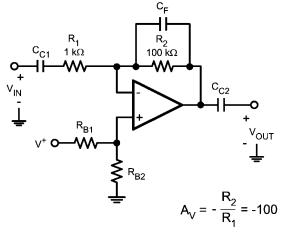
■ Output swing with 2 kΩ load 120 mV from rail

■ Total harmonic distortion 0.003% @ 1 kHz, 2 kΩ

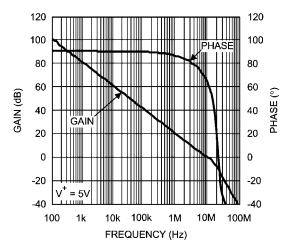
■ Temperature range -40°C to 125°C

Applications

- Portable equipment
- Automotive
- Battery powered systems
- Sensors and Instrumentation



High Gain Wide Bandwidth Inverting Amplifier



Open Loop Gain and phase vs. Frequency

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

ESD Tolerance (Note 2)

Junction Temperature (Note 3)

 Soldering Information

Infrared or Convection (20 sec) 235°C

Wave Soldering Lead Temp (10

sec) 260°C

Operating Ratings (Note 1)

Temperature Range (Note 3) -40°C to 125°C Supply Voltage 2.7V to 5.5V

Package Thermal Resistance (θ_{JA}) (Note 3)

5-Pin SC70 456°C/W 14-Pin TSSOP 160°C/W

3V DC Electrical Characteristics

Unless otherwise specified, all limits are guaranteed for $T_A = 25^{\circ}C$, $V^+ = 3V$, $V^- = 0V$, $V_O = V_{CM} = V^+/2$, and $R_L > 1$ M Ω . **Boldface** limits apply at the temperature extremes.

+150°C

Symbol	Parameter	Conditions	Min (Note 5)	Typ (Note 4)	Max (Note 5)	Units	
V _{OS}	Input Offset Voltage			0.1	±1.5 2.7	mV	
TC V _{os}	Input Offset Average Drift			6.6		μV/°C	
I _B	Input Bias Current	(Note 6)		80	120	nA	
I _{os}	Input Offset Current			2.2	15	nA	
CMRR	Common Mode Rejection Ratio	0 ≤ V _{CM} ≤ 2.0 V	87 80	100		dB	
PSRR	Power Supply Rejection Ratio	$3.0 \le V^{+} \le 5V, V_{CM} = 0.5$	87 81	95		dB	
		$2.7 \le V^{+} \le 5.5V, V_{CM} = 0.5$	87 81	95			
CMVR	Input Common-Mode Voltage Range	CMRR ≥ 75 dB CMRR ≥ 60 dB	0 0		2.1 2.1	V	
A _{VOL}	Large Signal Voltage Gain	$0.3 \le V_O \le 2.7$, $R_L = 2 \text{ k}\Omega \text{ to V+/2}$ $0.4 \le V_O \le 2.6$, $R_L = 2 \text{ k}\Omega \text{ to V+/2}$	80 76	85		-ID	
		$0.3 \le V_O \le 2.7$, $R_L = 10 \text{ k}\Omega$ to V+/2 $0.4 \le V_O \le 2.6$, $R_L = 10 \text{ k}\Omega$ to V+/2	86 83	93		- dB	
V _o	Output Swing High	$R_L = 2 \text{ k}\Omega \text{ to V+/2}$		80	95 120		
		$R_L = 10 \text{ k}\Omega \text{ to V+/2}$		45	50 60	mV from	
	Output Swing Low	$R_L = 2 \text{ k}\Omega \text{ to V+/2}$		95	110 125	rail	
		$R_L = 10 \text{ k}\Omega \text{ to V+/2}$		60	65 75		
I _{sc}	Maximum Continuous Output	Sourcing (Note 8)		17		- mA	
	Current	Sinking (Note 8)		25		ША	
Is	Supply Current per Amplifier	LMV651		115	140		
		LMV652		118	175	μΑ	
		LMV654		122			
SR	Slew Rate	A _V = +1, 10% to 90% (Note 7)		3.0		V/µs	
GBW	Gain Bandwidth Product			12		MHz	
e _n	Input-Referred Voltage Noise	f = 100 kHz		17		nV/√Hz	

Symbol	Parameter	Conditions	Min (Note 5)	Typ (Note 4)	Max (Note 5)	Units
i _n	Input-Referred Current Noise	f = 100 kHz		0.1		A / /U=
		f = 1 kHz		0.15		pA/√Hz
THD	Total Harmonic Distortion	$f = 1 \text{ kHz}, A_V = 2, R_L = 2 \text{ k}\Omega$		0.003		%

5V DC Electrical Characteristics

Unless otherwise specified, all limits are guaranteed for $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_O = V_{CM} = V^+/2$, and $R_L > 1$ M Ω . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min (Note 5)	Typ (Note 4)	Max (Note 5)	Units
V _{OS}	Input Offset Voltage			0.1	±1.5 2.7	mV
TC V _{OS}	Input Offset Average Drift			6.6		μV/°C
I _B	Input Bias Current	(Note 6)		80	120	nA
I _{os}	Input Offset Current			2.2	15	nA
CMRR	Common Mode Rejection Ratio	0 ≤ V _{CM} ≤ 4.0 V	90 83	100		dB
PSRR	Power Supply Rejection Ratio	$3V \le V^{+} \le 5V$, $V_{CM} = 0.5V$	87 81	95		dB
		2.7V ≤ V+ ≤ 5.5V, V _{CM} = 0.5V	87 81	95		
CMVR	Input Common-Mode Voltage Range	CMRR ≥ 80 dB CMRR ≥ 68 dB	0 0		4.1 4.1	V
A _{VOL}	Large Signal Voltage Gain	$0.3 \le V_O \le 4.7V$, $R_L = 2 \text{ k}\Omega \text{ to V+/2}$ $0.4 \le V_O \le 4.6$, $R_L = 2 \text{ k}\Omega \text{ to V+/2}$	79 76	84		dП
		$0.3 \le V_O \le 4.7V$, $R_L = 10 kΩ$ to V+/2 $0.4 \le V_O \le 4.6$, $R_L = 10 kΩ$ to V+/2	87 84	94		- dB
V _O	Output Swing High Output Swing Low	$R_L = 2 k\Omega$ to V+/2		120	140 185	
		$R_L = 10 \text{ k}\Omega \text{ to V+/2}$		75	90 120	mV from
		$R_L = 2 k\Omega$ to V+/2		110	130 150	rail
		$R_L = 10 \text{ k}\Omega \text{ to V+/2}$		70	80 95	
I _{sc}	Maximum Continuous Output Current	Sourcing (Note 8)		18.5		m A
		Sinking (Note 8)		25		mA
I _S	Supply Current per Amplifier	LMV651 LMV652		116 118	140 175	μΑ
SR	Slew Rate	LMV654 $A_{V} = +1, V_{O} = 1 V_{PP}$		3.0		V/µs
GBW	Gain Bandwidth Product	10% to 90% (Note 7)		12		MHz
e _n	Input-Referred Voltage Noise	f = 100 kHz	+	17		nV/√Hz
		f = 1 kHz		17		
${i_n}$	Input-Referred Current Noise	f = 100 kHz		0.1		+
'n	Impat Holonou oullont Noise	f = 1 kHz		0.15		pA/√Hz
THD	Total Harmonic Distortion	$f = 1 \text{ kHz}, A_V = 2, R_L = 2 \text{ k}\Omega$		0.003		%

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics Tables

Note 2: Human Body Model, applicable std. MIL-STD-883, Method 3015.7. Machine Model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC) Field-Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC).

Note 3: The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A) / \theta_{JA}$. All numbers apply for packages soldered directly onto a PC board.

Note 4: Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.

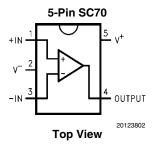
Note 5: Limits are 100% production tested at 25°C. Limits over the operating temperature range are guaranteed through correlations using Statistical Quality Control (SQC) method.

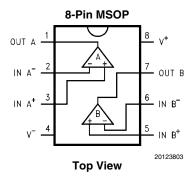
Note 6: Positive current corresponds to current flowing into the device.

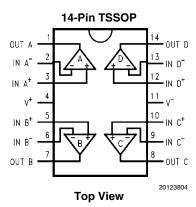
Note 7: Slew rate is the average of the rising and falling slew rates.

Note 8: The part is not short circuit protected and is not recommended for operation with low resistive loads. Typical sourcing and sinking output current curves are provided in the Typical Performance Characteristics and should be consulted before designing for heavy loads.

Connection Diagrams







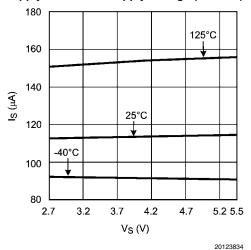
Ordering Information

Package	Part Number	Package Marking	Transport Media	NSC Drawing	
5-Pin SC70	LMV651MG	A93	1k Units Tape and Reel	MAA05A	
5-PIII 5C/U	LMV651MGX	A93	3k Units Tape and Reel		
8-Pin MSOP	LMV652MM	AB3A	1k Units Tape and Reel	MUA08A	
0-PIII WISOP	LMV652MMX	ABSA	3.5k Units Tape and Reel		
14-Pin TSSOP	LMV654MT	LMV654MT	94 Units/Rail	MTC14	
14-PIII 1550P	LMV654MTX	LIVI V 034IVI I	2.5k Units Tape and Reel	W11014	

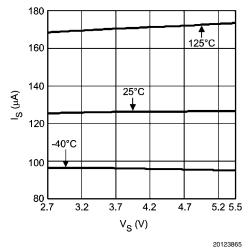
Typical Performance Characteristics Unless otherwise Specified, $T_A = 25$ °C, $V_S = 5$ V, $V^+ = 5$ V, $V^- = 0$ V,

 $V_{CM} = V_S/2$

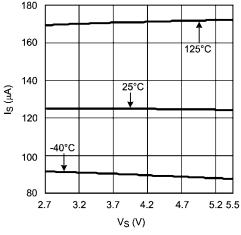
Supply Current vs. Supply Voltage (LMV651)



Supply Current per Channel vs. Supply Voltage (LMV652)

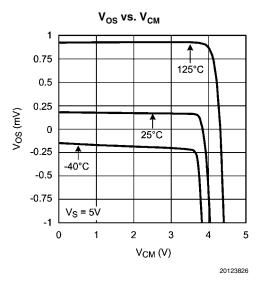


Supply Current per Channel vs. Supply Voltage (LMV654)

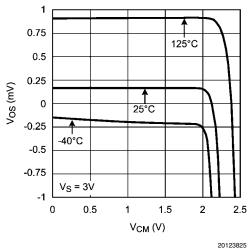


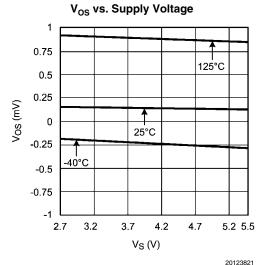
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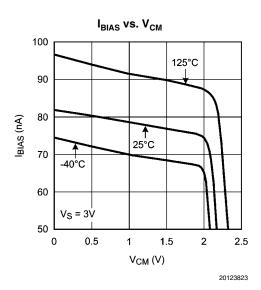
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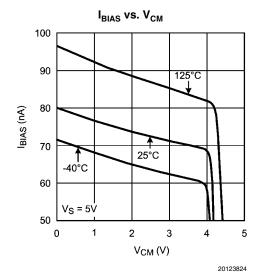


 ${
m V}_{
m OS}$ vs. ${
m V}_{
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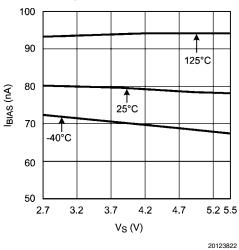




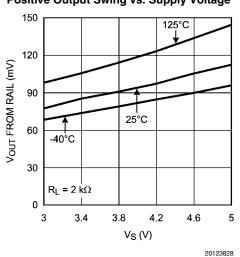




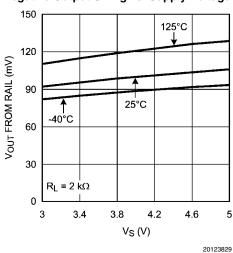




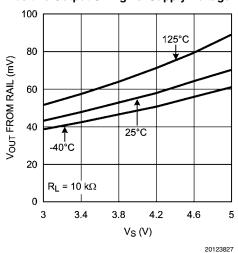
Positive Output Swing vs. Supply Voltage



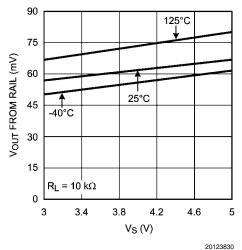
Negative Output Swing vs. Supply Voltage



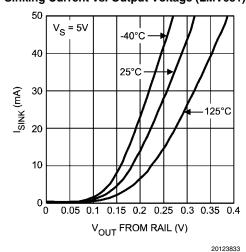
Positive Output Swing vs. Supply Voltage



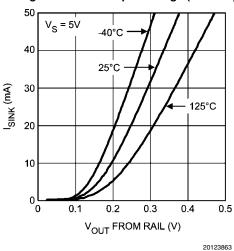
Negative Output Swing vs. Supply Voltage



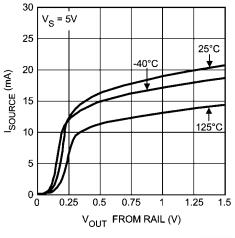
Sinking Current vs. Output Voltage (LMV651)



Sinking Current vs. Output Voltage (LMV654)

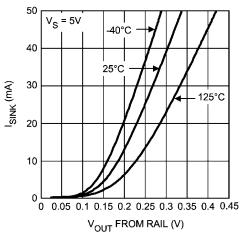


Sourcing Current vs. Output Voltage



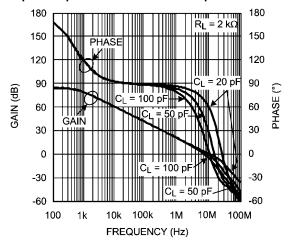
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Sinking Current vs. Output Voltage (LMV652)



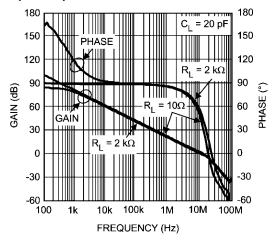
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Open Loop Gain and Phase with Capacitive Load

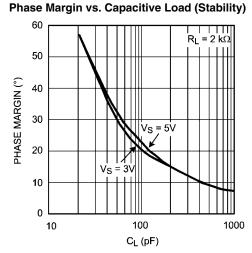


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Open Loop Gain and Phase with Resistive Load

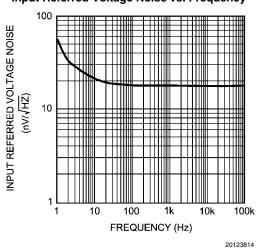


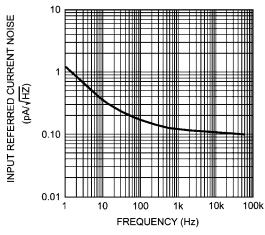
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Input Referred Voltage Noise vs. Frequency

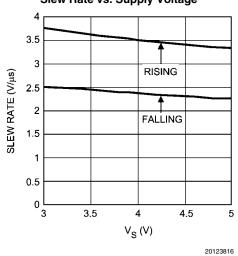




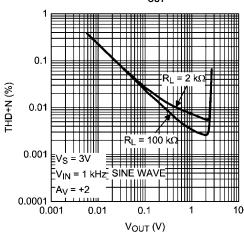
Input Referred Current Noise vs. Frequency



Slew Rate vs. Supply Voltage



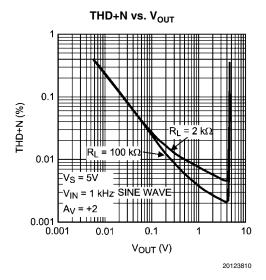
THD+N vs. V_{OUT}

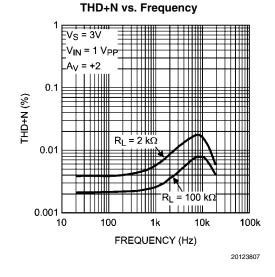


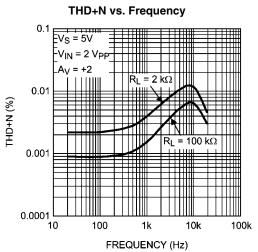
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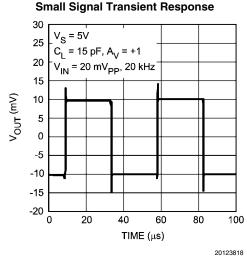
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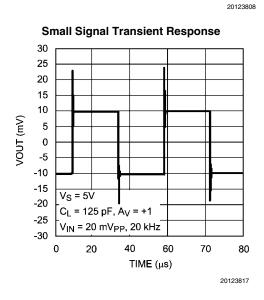
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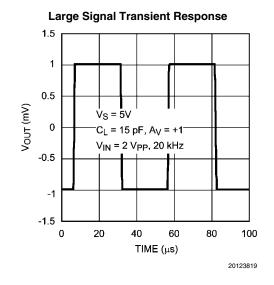




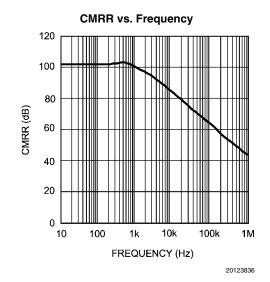




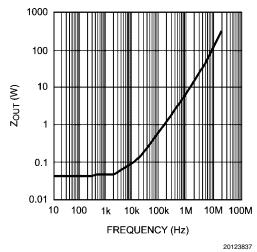




PSRR vs. Frequency 120 V_S = 5V, +PSRR V_S 100 80 PSRR (dB) $V_S = 3V$, -PSRR 60 40 20 0 10 100 1k 10k 100k 1M 10M FREQUENCY (Hz) 20123835



Closed Loop Output Impedance vs. Frequency



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Application Information

ADVANTAGES OF THE LMV651/LMV652/LMV654

Low Voltage and Low Power Operation

The LMV651/LMV652/LMV654 have performance guaranteed at supply voltages of 3V and 5V. These parts are guaranteed to be operational at all supply voltages between 2.7V and 5.5V. The LMV651 draws a low supply current of 116 μA , the LMV652 draws 118 $\mu\text{A}/\text{channel}$ and the LMV654 draws 122 $\mu\text{A}/\text{channel}$. This family of op amps provides the low voltage and low power amplification which is essential for portable applications.

Wide Bandwidth

Despite drawing the very low supply current of 116 μA , the LMV651/LMV652/LMV654 manage to provide a wide unity gain bandwidth of 12 MHz. This is easily one of the best bandwidth to power ratios ever achieved, and allows these op amps to provide wideband amplification while using the minimum amount of power. This makes this family of parts ideal for low power signal processing applications such as portable media players and other accessories.

Low Input Referred Noise

The LMV651/LMV652/LMV654 provide <u>a flatband</u> input referred voltage noise density of 17 nV/ $\sqrt{\rm Hz}$, which is significantly better than the noise performance expected from a low power op amp. These op amps also feature exceptionally low 1/f noise, with a very low 1/f noise corner frequency of 4 Hz. This makes these parts ideal for low power applications which require decent noise performance, such as PDAs and portable sensors.

Ground Sensing and Rail-to-Rail Output

The LMV651/LMV652/LMV654 each have a rail-to-rail output stage, which provides the maximum possible output dynamic range. This is especially important for applications requiring a large output swing. The input common mode range of this family of devices includes the negative supply rail which allows direct sensing at ground in a single supply operation.

Small Size

The small footprint of the packages for the LMV651/LMV652/LMH654 saves space on printed circuit boards, and enables the design of smaller and more compact electronic products. Long traces between the signal source and the op amp make the signal path susceptible to noise. By using a physically smaller package, these op amps can be placed closer to the signal source, reducing noise pickup and enhancing signal integrity.

STABILITY OF OP AMP CIRCUITS

Stability and Capacitive Loading

If the phase margin of the LMV651/LMV652/LMV654 is plotted with respect to the capacitive load (C_L) at its output, it is seen that the phase margin reduces significantly if C_L is increased beyond 100 pF. This is because the op amp is designed to provide the maximum bandwidth possible for a low supply current. Stabilizing it for higher capacitive loads would have required either a drastic increase in supply current, or a large internal compensation capacitance, which would have reduced the bandwidth of the op amp. Hence, if these devices are to be used for driving higher capacitive loads, they would have to be externally compensated.

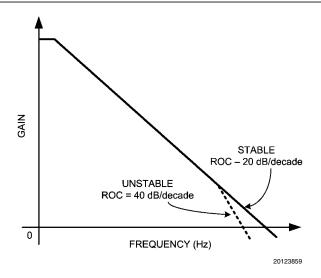


FIGURE 1. Gain vs. Frequency for an Op Amp

An op amp, ideally, has a dominant pole close to DC, which causes its gain to decay at the rate of 20 dB/decade with respect to frequency. If this rate of decay, also known as the rate of closure (ROC), remains the same until the op amp's unity gain bandwidth, the op amp is stable. If, however, a large capacitance is added to the output of the op amp, it combines with the output impedance of the op amp to create another pole in its frequency response before its unity gain frequency (Figure 1). This increases the ROC to 40 dB/decade and causes instability.

In such a case a number of techniques can be used to restore stability to the circuit. The idea behind all these schemes is to modify the frequency response such that it can be restored to an ROC of 20 dB/decade, which ensures stability.

In The Loop Compensation

Figure 2 illustrates a compensation technique, known as 'in the loop' compensation, that employs an RC feedback circuit within the feedback loop to stabilize a non-inverting amplifier configuration. A small series resistance, $R_{\rm S}$, is used to isolate the amplifier output from the load capacitance, $C_{\rm L}$, and a small capacitance, $C_{\rm F}$, is inserted across the feedback resistor to bypass $C_{\rm L}$ at higher frequencies.

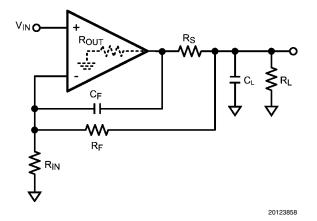


FIGURE 2. In the Loop Compensation

The values for R_S and C_F are decided by ensuring that the zero attributed to C_F lies at the same frequency as the pole attributed to C_L . This ensures that the effect of the second pole on the transfer function is compensated for by the presence of the zero, and that the ROC is maintained at 20 dB/decade. For the circuit shown in Figure 2 the values of R_S and C_F are given by Equation 1. Values of R_S and C_F required for maintaining stability for different values of C_L , as well as the phase margins obtained, are shown in Table 1. R_F and $R_{\rm IN}$ are taken to be 10 k Ω , R_L is 2 k Ω , while $R_{\rm OUT}$ is taken as 340Ω .

$$R_{S} = \frac{R_{OUT}R_{IN}}{R_{F}}$$

$$C_{F} = \left(\frac{R_{F} + 2R_{IN}}{R_{F}^{2}}\right)C_{L}R_{OUT}$$
(1)

TABLE 1.

C _L (pF)	R _S (Ω)	C _F (pF)	Phase Margin (°)
150	340	15	39.4
200	340	20	34.6
250	340	25	31.1

Although this methodology provides circuit stability for any load capacitance, it does so at the price of bandwidth. The closed loop bandwidth of the circuit is now limited by $\rm R_{\rm F}$ and $\rm C_{\rm F}.$

Compensation By External Resistor

In some applications it is essential to drive a capacitive load without sacrificing bandwidth. In such a case, in the loop compensation is not viable. A simpler scheme for compensation is shown in Figure 3. A resistor, $R_{\rm ISO}$, is placed in series between the load capacitance and the output. This introduces a zero in the circuit transfer function, which counteracts the effect of the pole formed by the load capacitance, and ensures stability. The value of $R_{\rm ISO}$ to be used should be decided depending on the size of C_L and the level of performance desired. Values ranging from 5Ω to 50Ω are usually sufficient to ensure stability. A larger value of $R_{\rm ISO}$ will result in a system with lesser ringing and overshoot, but will also limit the output swing and the short circuit current of the circuit.

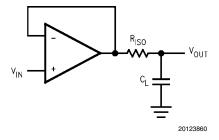


FIGURE 3. Compensation by Isolation Resistor

Typical Applications

HIGH GAIN LOW POWER AMPLIFIERS

With a low supply current, low power operation, and low harmonic distortion, the LMV651/LMV652/LMV654 are ideal for wide-bandwidth, high gain amplification. The wide unity gain bandwidth allows these parts to provide large gain over a wide frequency range, while driving loads as low as 2 $k\Omega$ with less

than 0.003% distortion. Two amplifier circuits are shown in Figure 4 and Figure 5. Figure 4 is an inverting amplifier, with a 100 k Ω feedback resistor, R_2 , and a 1 k Ω input resistor, R_1 , and provides a gain of –100. With the LMV651/LMV652/LMV654 these circuits can provide gain of –100 with a –3 dB bandwidth of 120 kHz, for a quiescent current as low as 116 μA . Similarly, the circuit in Figure 5, a non-inverting amplifier with a gain of 1001, can provide that gain with a –3 dB bandwidth of 12 kHz, for a similar low quiescent power dissipation. Coupling capacitors C_{C1} and C_{C2} can be added to isolate the circuit from DC voltages, while R_{B1} and R_{B2} provide DC biasing. A feedback capacitor C_{F} can also be added to improve compensation.

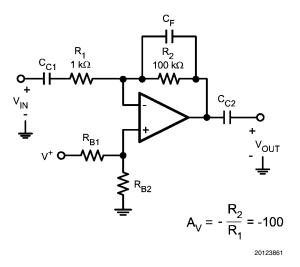


FIGURE 4. High Gain Inverting Amplifier

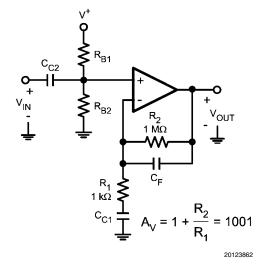


FIGURE 5. High Gain Non-Inverting Amplifier

ACTIVE FILTERS

With a wide unity gain bandwidth of 12 MHz, low input referred noise density and a low power supply current, the LMV651/LMV652/LMV654 are well suited for low-power filtering applications. Active filter topologies, like the Sallen-Key low pass filter shown in *Figure 6*, are very versatile, and can be used to design a wide variety of filters (Chebyshev, Butterworth or Bessel). The Sallen-Key topology, in particular, can be used to attain a wide range of Q, by using positive feedback to reject the undesired frequency range.

In the circuit shown in Figure 6, the two capacitors appear as open circuits at lower frequencies and the signal is simply buffered to the output. At high frequencies the capacitors appear as short circuits and the signal is shunted to ground by one of the capacitors before it can be amplified. Near the cutoff frequency, where the impedance of the capacitances is on the same order as $\rm R_g$ and $\rm R_f$, positive feedback through the other capacitor allows the circuit to attain the desired Q. The ratio of the two resistors, $\rm m^2$, provides a knob to control the value of Q obtained.

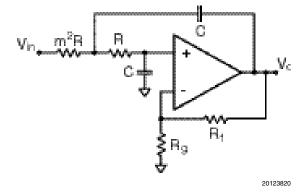
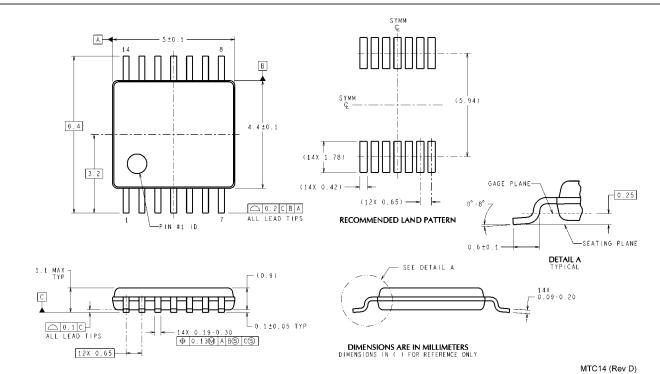


FIGURE 6.

Physical Dimensions inches (millimeters) unless otherwise noted 1.25±0.1 - 5X 0.15-0.30 ⊕ 0.1₩ CBS AS LAND PATTERN RECOMMENDATION GAGE PLANE Ç □ 0.1 C 0.4±0.05 TYP (0,515 TYP) DIMENSIONS ARE IN MILLIMETERS MAA05A (Rev C) 5-Pin SC70 **NS Package Number MAA05A** 8 Ç .193±.006 [4.9±0.15] PIN 1 IDENT LAND PATTERN RECOMMENDATION 6X .0256 [0.65] GAGE PLANE R.005 TYP △ .004 [0.1] A L 0° - 6° TYP .021±.005 [0.53±0.12] TYP -SEATING PLANE (.0375 TYP [0.953] CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS MUA08A (Rev E) 8-Pin MSOP **NS Package Number MUA08A**



14-Pin TSSOP NS Package Number MTC14

Notes

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